

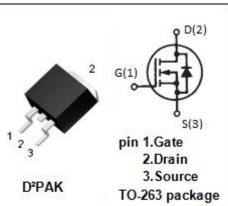
INCHANGE SEMICONDUCTOR

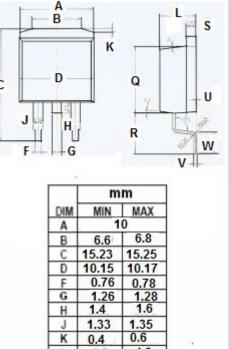
isc N-Channel MOSFET Transistor

IXTA220N075T

| Ros(c • Fully ch • 100% a • Minimu | rain-source on-resistance: on) $\leq 4.5 m \Omega @V_{GS} = 10V$ aracterized avalanche voltage and valanche tested m Lot-to-Lot variations for robust of ance and reliable operation | | | 1 2 3 D ² P | AK | | (1) oin 1.Ga 2.Da 3.Sa 10-263 |
|---|---|---------|------|---------------------------|-------------|-----------------------|---|
| | Converters | | | | | | |
| • High Ci | Irrent Switching Applications | - A | | | A | - 1 | |
| • ABSOL | • ABSOLUTE MAXIMUM RATINGS(Ta=25°C) | | | | В | 1 | 1 |
| SYMBOL | PARAMETER | VALUE | UNIT | | | ĸ | |
| V _{DSS} | Drain-Source Voltage | 75 | V | c | D | | Q Z |
| V _{GS} | Gate-Source Voltage | ±20 | V | | H | ſ | R |
| I _D | Drain Current-Continuous | 220 | А | | | | |
| I _{DM} | Drain Current-Single Pulsed | 600 | А | | DIM | MIN | MAX 0 |
| P _D | Total Dissipation @T _C =25℃ | 480 | W | _ | A B C | 6.6 15.23 | 6.8 15.25 |
| Tj | Operating Junction Temperature | -55~175 | °C | | D F G | 10.15 0.76 1.26 | 10.17 0.78 1.28 |
| T _{stg} | Storage Temperature | -55~175 | °C | _ | H | 1.4 1.33 | 1.6 1.35 |
| | IAL CHARACTERISTICS | | | - | L | 0.4 4.6 8.69 | 0.6 4.8 8.71 |

| SYMBOL | PARAMETER | MAX | UNIT | | |
|----------------------|-------------------------------------|------|------|--|--|
| R _{th(j-c)} | Junction-to-case thermal resistance | 0.31 | °C/W | | |





1.26

0.0

0.37

W 2.80

s U

V

1.28

0.2

0.39

2.82



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | МАХ | UNIT |
|---------------------|--------------------------------|--|-----|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; ID = 250 μ A | 75 | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | V _{DS} =V _{GS} ; ID = 250 μ A | 2.0 | 4.0 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =10V; I _D = 25A | | 4.5 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} = ±20V;V _{DS} =0V | | ±200 | nA |
| | Drain-Source Leakage Current | V _{DS} = V _{DSS} ; V _{GS} = 0V | | 5 | μA |
| I _{DSS} | Diani-Source Leakage Current | V _{DS} = V _{DSS} ; V _{GS} = 0V;TJ= 150℃ | | 250 | μA |
| V_{SD} | Diode forward voltage | I _F = 25A; V _{GS} = 0V | | 1.0 | V |

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